

# Amplifier Transistors

## PNP Silicon

### L2N5401

#### MAXIMUM RATINGS

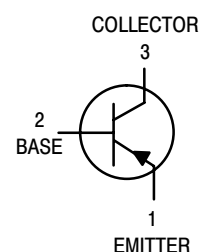
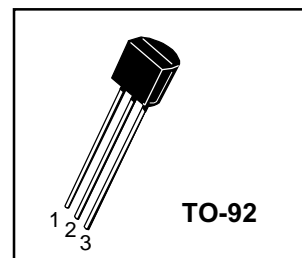
Rating	Symbol	2N5401	Unit
Collector – Emitter Voltage	$V_{CEO}$	150	Vdc
Collector – Base Voltage	$V_{CBO}$	160	Vdc
Emitter – Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current – Continuous	$I_C$	600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

**L2N5401**



#### MARKING DIAGRAM



Y = Year  
WW = Work Week

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### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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#### OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage <sup>(1)</sup> ( $I_C = 1.0\text{ mAdc}$ , $I_E = 0$ )	$V_{(BR)CEO}$	150	–	Vdc
Collector–Base Breakdown Voltage ( $I_C = 100\text{ }\mu\text{Adc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	160	–	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10\text{ }\mu\text{Adc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	5.0	–	Vdc
Collector Cutoff Current ( $V_{CB} = 120\text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 120\text{ Vdc}$ , $I_E = 0$ , $T_A = 100^\circ\text{C}$ )	$I_{CBO}$	– –	50 50	
Emitter Cutoff Current ( $V_{EB} = 3.0\text{ Vdc}$ , $I_C = 0$ )	$I_{EBO}$	–	50	nAdc

#### ON CHARACTERISTICS (Note 1)

DC Current Gain ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ ) ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ ) ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 5.0\text{ Vdc}$ )	$h_{FE}$	50 60 50	– 240 –	–
Collector–Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ ) ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )	$V_{CE(sat)}$	– –	0.2 0.5	Vdc
Base–Emitter Saturation Voltage ( $I_C = 10\text{ mAdc}$ , $I_B = 1.0\text{ mAdc}$ ) ( $I_C = 50\text{ mAdc}$ , $I_B = 5.0\text{ mAdc}$ )	$V_{BE(sat)}$	– –	1.0 1.0	Vdc

#### SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = 10\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 100\text{ MHz}$ )	$f_T$	100	300	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	–	6.0	pF
Small–Signal Current Gain ( $I_C = 1.0\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	40	200	–
Noise Figure ( $I_C = 250\text{ }\mu\text{Adc}$ , $V_{CE} = 5.0\text{ Vdc}$ , $R_S = 1.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ )	NF	–	8.0	dB

1. Pulse Test: Pulse Width  $\leq 300\text{ }\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

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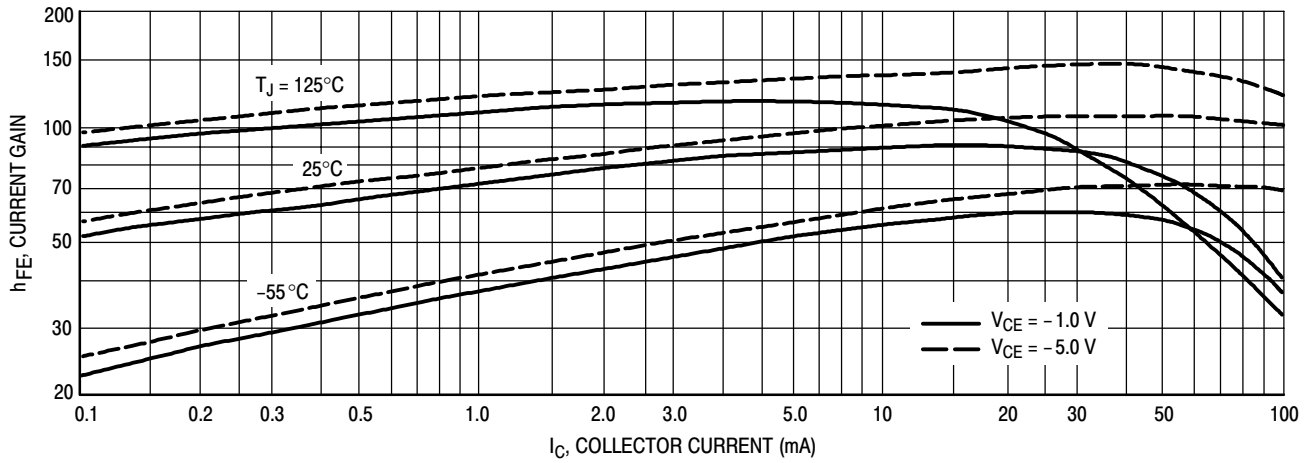


Figure 1. DC Current Gain

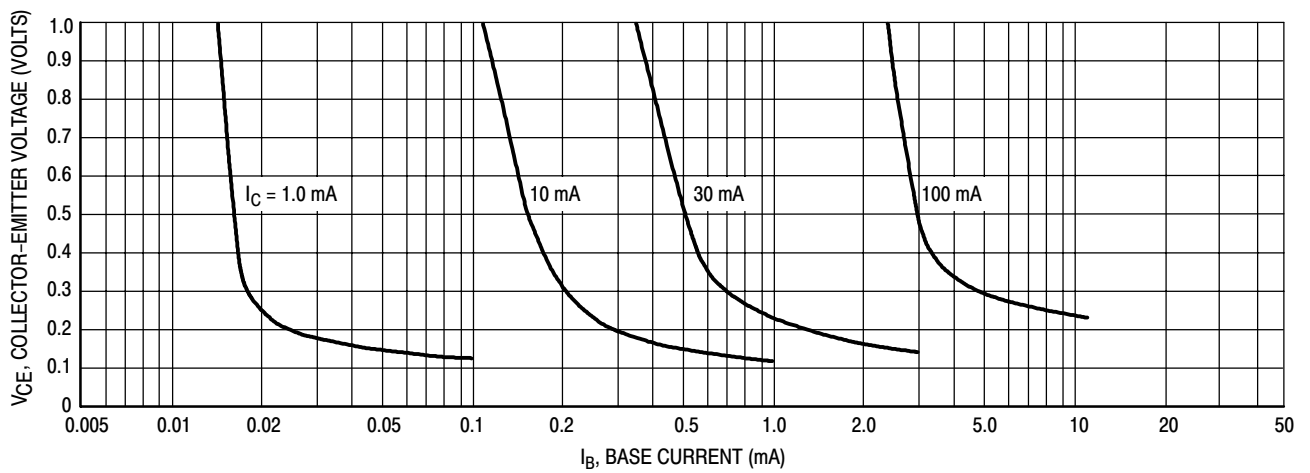


Figure 2. Collector Saturation Region

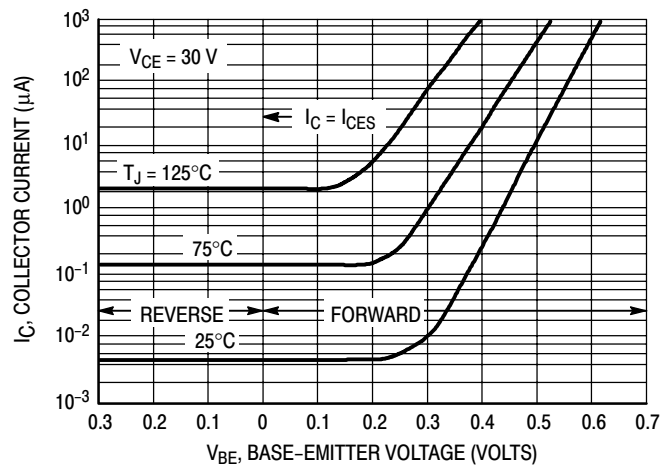


Figure 3. Collector Cut-Off Region

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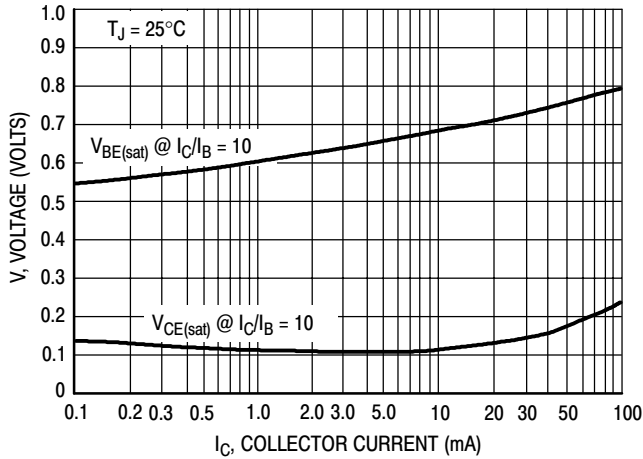


Figure 4. "On" Voltages

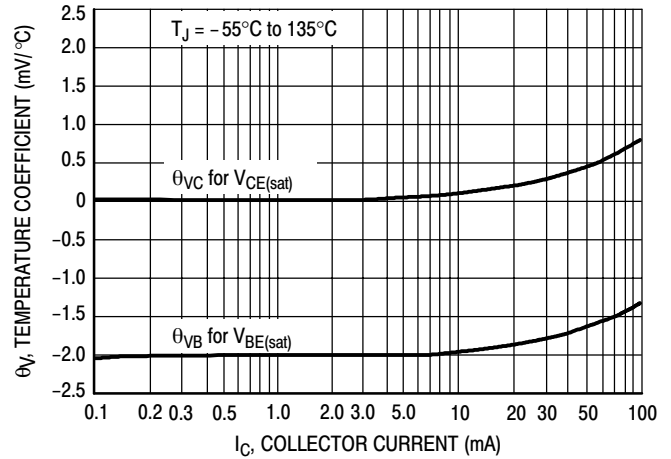


Figure 5. Temperature Coefficients

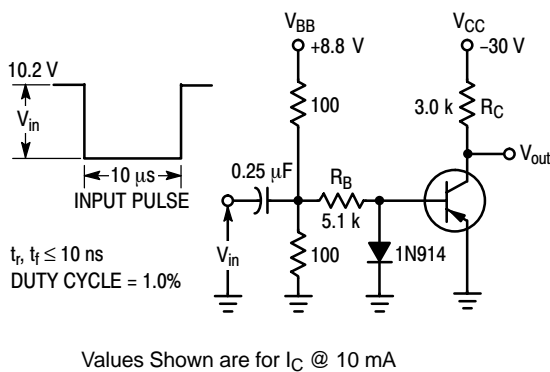


Figure 6. Switching Time Test Circuit

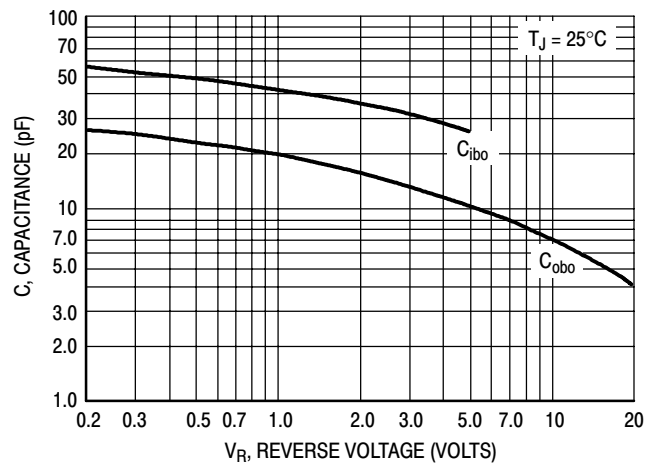


Figure 7. Capacitances

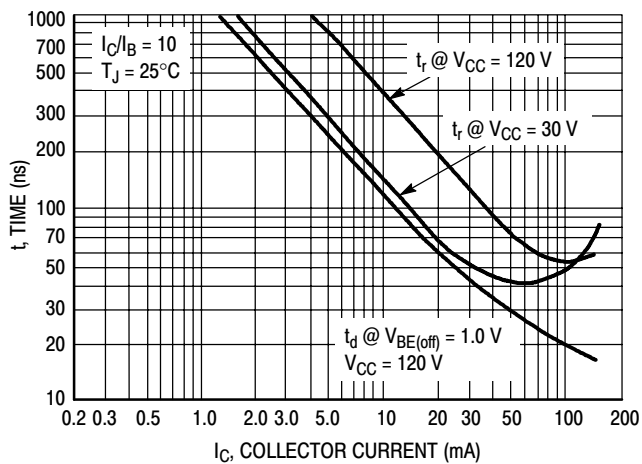


Figure 8. Turn-On Time

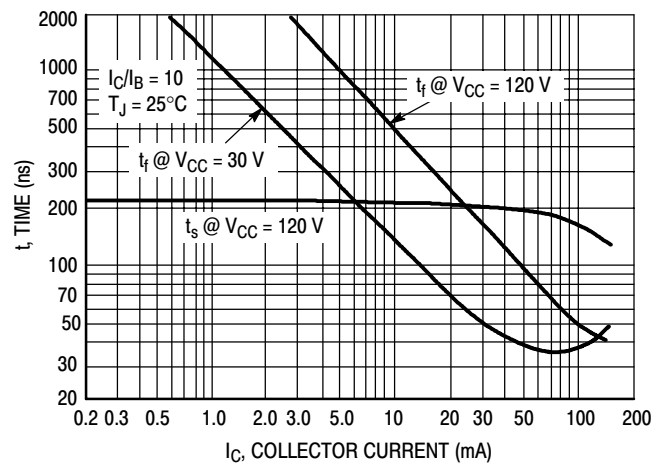


Figure 9. Turn-Off Time